

This listing of claims will replace all prior versions, and listings, of claims in the application:

The Status of the Claims

1. (Currently amended): A method for manufacturing a semiconductor device, the method comprising:
 successively depositing gate insulating layer forming material and gate electrode forming material on a semiconductor substrate;
 patterning the gate insulating layer forming material and the gate electrode forming material to form a gate insulating layer and a gate electrode;
 performing a nitrogen ion-implantation to a front face of the substrate and the gate electrode after the forming of the gate insulating layer and the gate electrode; and
 annealing the substrate so as to form a re-oxidation layer that has different thickness on the sidewalls of the gate electrode than on the substrate; and
 forming source/drain regions after the annealing of the substrate.
2. (Previously presented): A method for manufacturing a semiconductor device as claimed in claim 1, wherein the nitrogen ion implantation is performed at an energy of 10 to 50keV.
3. (Original): A method for manufacturing a semiconductor device as claimed in claim 1, wherein dose of nitrogen ion implantation is 10^{14} to 5×10^{15} atoms/cm².
4. (Original): A method for manufacturing a semiconductor device as claimed in claim 1, wherein an angle of nitrogen ion implantation is vertical to the substrate.

5. (Previously presented): A method for manufacturing a semiconductor device as claimed in claim 4, wherein the nitrogen ion implantation is performed at an energy of 10 to 50keV.

6. (Original): A method for manufacturing a semiconductor device as claimed in claim 4, wherein dose of nitrogen ion implantation is 10^{14} to 5×10^{15} atoms/cm².

7. (Canceled)

8. (Currently amended) A method for manufacturing a semiconductor device, the method comprising:
successively depositing gate insulating layer forming material and gate electrode forming material on a semiconductor substrate;
patterning the gate insulating layer forming material and the gate electrode forming material to form a gate insulating layer and a gate electrode;
performing a nitrogen ion-implantation to a front face of the substrate and the gate electrode after the forming of the gate insulating layer and the gate electrode;
annealing the substrate so as to form a re-oxidation layer that has different thickness on the sidewalls of the gate electrode than on the substrate; and
forming an LDD structure after the annealing the substrate.

9. (Previously presented): The method for manufacturing a semiconductor device as claimed in claim 8, wherein the nitrogen ion-implantation is performed at an energy of 10 to 50keV.

10. (Previously presented): The method for manufacturing a semiconductor device as claimed in claim 8, wherein dose of nitrogen ion implantation is 10^{14} to 5×10^{15} atoms/cm².

11. (Previously presented): A method for manufacturing a semiconductor device as claimed in claim 8, wherein an angle of nitrogen ion implantation is vertical to the substrate.
12. (Previously presented): A method for manufacturing a semiconductor device as claimed in claim 11, wherein the nitrogen ion-implantation is performed at an energy of 10 to 50keV.
13. (Previously presented): A method for manufacturing a semiconductor device as claimed in claim 11, wherein dose of nitrogen ion implantation is 10^{14} to 5×10^{15} atoms/cm².